



FEATURES

- Access time : 35/55/70ns (max.)
- Low power consumption :
 Operating : 60/50/40 mA (typical)
 Standby : 10μA (typical) L-version
 1μA (typical) LL-version
- Wide range power supply : 2.7V to 5.5V
- All inputs and outputs TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 32-pin 600 mil PDIP
 32-pin 450 mil SOP
 32-pin 8x20mm TSOP-1
 32-pin 8x13.4mm STSOP

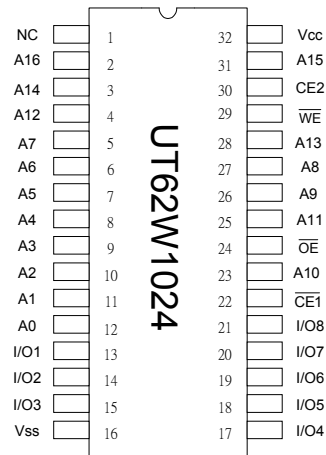
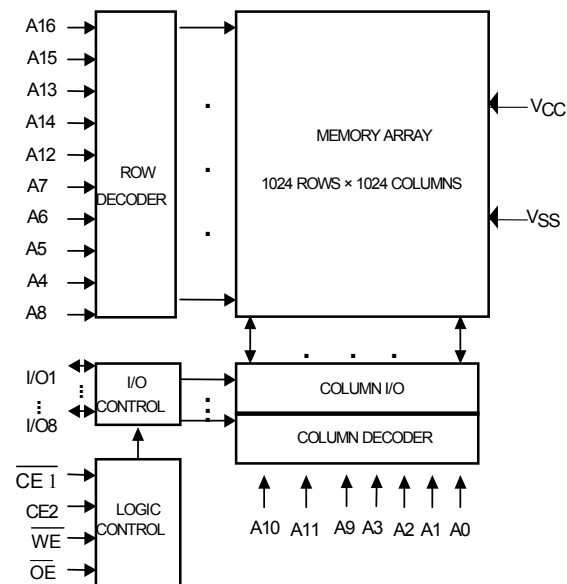
The UT62W1024 is a 1,048,576-bit low power CMOS static random access memory organized as 131,072 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

The UT62W1024 is designed for low power application. It is particularly well suited for battery back-up nonvolatile memory application.

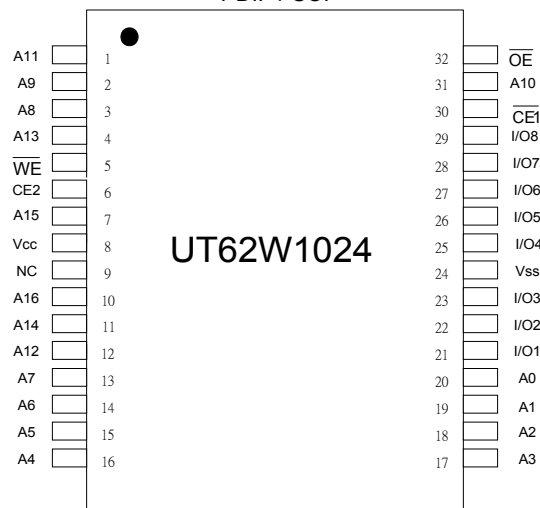
The UT62W1024 operates from a wide range of 2.7V~ 5.5V power supply and all inputs and outputs are fully TTL compatible.

PIN CONFIGURATION

FUNCTIONAL BLOCK DIAGRAM



PDIP / SOP



TSOP-I/STSOP

PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A16	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
CE1, CE2	Chip enable 1,2 Inputs
WE	Write Enable Input
OE	Output Enable Input
V _{CC}	Power Supply
V _{SS}	Ground
NC	No Connection

GENERAL DESCRIPTION



ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.5 to +4.6	V
Operating Temperature	T _A	0 to +70	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA
Soldering Temperature (under 10 sec)	T _{solder}	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE ₁	CE ₂	OE	WE	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	X	High - Z	I _{SB} , I _{SB1}
Standby	X	L	X	X	High - Z	I _{SB} , I _{SB1}
Output Disable	L	H	H	H	High - Z	I _{CC}
Read	L	H	L	H	D _{OUT}	I _{CC}
Write	L	H	X	L	D _{IN}	I _{CC}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS (I) (V_{CC} = 2.7V~3.6V, V_{SS}=0V, T_A = 0°C to 70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT			
Input High Voltage	V _{IH}		2.0	-	V _{CC} +0.5	V			
Input Low Voltage	V _{IL}		-0.5	-	0.6	V			
Input Leakage Current	I _{IL}	V _{SS} ≤ V _{IN} ≤ V _{CC}	-1	-	1	μA			
Output Leakage Current	I _{OL}	V _{SS} ≤ V _{I/O} ≤ V _{CC} CE ₁ = V _{IH} or CE ₂ = V _{IL} or OE = V _{IH} or WE = V _{IL}	-1	-	1	μA			
Output High Voltage	V _{OH}	I _{OH} = -1mA	2.2	-	-	V			
Output Low Voltage	V _{OL}	I _{OL} = 4mA	-	-	0.4	V			
Average Operating Power Supply Current	I _{CC}	Cycle time = Min. 100% Duty, CE ₁ = V _{IL} , CE ₂ = V _{IH} , I _{I/O} = 0mA	-35	-	40	60	mA		
			-55	-	35	50	mA		
			-70	-	30	40	mA		
	I _{CC1}	Cycle time = 1μs, 100% Duty, CE ₁ ≤ 0.2V, CE ₂ ≥ V _{CC} -0.2V, , C _L =50PF	-	-	5	mA			
Standby Power Supply Current	I _{SB}	CE ₁ = V _{IH} or CE ₂ = V _{IL}	-	-	1.0	mA			
			I _{SB1}	CE ₁ ≥ V _{CC} -0.2V or CE ₂ ≤ 0.2V	-L	-	2.5	100 20*	μA
					-LL	-	0.5	40 10*	μA

*Those parameters are for reference only under 50°C



DC ELECTRICAL CHARACTERISTICS (II) ($V_{CC} = 4.5V \sim 5.5V, V_{SS} = 0V, T_A = 0^\circ C \text{ to } 70^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Input High Voltage	V_{IH}		2.2	-	$V_{CC} + 0.5$	V	
Input Low Voltage	V_{IL}		-0.5	-	0.8	V	
Input Leakage Current	I_{IL}	$V_{SS} \leq V_{IN} \leq V_{CC}$	-1	-	1	μA	
Output Leakage Current	I_{OL}	$V_{SS} \leq V_{IO} \leq V_{CC}$ $\overline{CE1} = V_{IH}$ or $CE2 = V_{IL}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$	-1	-	1	μA	
Output High Voltage	V_{OH}	$I_{OH} = -1mA$	2.4	-	-	V	
Output Low Voltage	V_{OL}	$I_{OL} = 4mA$	-	-	0.4	V	
Average Operating Power Supply Current	I_{CC}	Cycle time = Min. 100% Duty, $\overline{CE1} = V_{IL}, CE2 = V_{IH},$, $C_L = 100PF$	-35	-	60	100	mA
			-55	-	50	85	mA
			-70	-	-40	70	mA
	I_{CC1}	Cycle time = $1\mu s$, 100% Duty, $\overline{CE1} \leq 0.2V, CE2 \geq V_{CC} - 0.2V,$ $I_{IO} = 0mA$	-	-	-	5	mA
Standby Power Supply Current	I_{SB}	$\overline{CE1} = V_{IH}$ or $CE2 = V_{IL}$	-	-	-	1.0	mA
			I_{SB1}	$\overline{CE1} \geq V_{CC} - 0.2V$ or $CE2 \leq 0.2V$	-L	-	2.5
	-LL	-			0.5	20*	40

*Those parameters are for reference only under $50^\circ C$

**CAPACITANCE** ($T_A=25^{\circ}\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L=100\text{pF}$, $I_{OH}/I_{OL}=-1\text{mA}/4\text{mA}$ ($V_{CC}=5\text{V}$) $C_L=50\text{pF}$, $I_{OH}/I_{OL}=-1\text{mA}/2\text{mA}$ ($V_{CC}=3.3\text{V}$)

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.7\text{V}\sim 5.5\text{V}$, $V_{SS}=0\text{V}$, $T_A = 0^{\circ}\text{C}$ to 70°C)**(1) READ CYCLE**

PARAMETER	SYMBOL	UT62W1024-35		UT62W1024-55		UT62W1024-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	35	-	55	-	70	-	ns
Address Access Time	t_{AA}	-	35	-	55	-	70	ns
Chip Enable Access Time	t_{ACE1} , t_{ACE2}	-	35	-	55	-	70	ns
Output Enable Access Time	t_{OE}	-	25	-	30	-	35	ns
Chip Enable to Output in Low-Z	t_{CLZ1}^* , t_{CLZ2}^*	10	-	10	-	10	-	ns
Output Enable to Output in Low-Z	t_{OLZ}^*	5	-	5	-	5	-	ns
Chip Disable to Output in High-Z	t_{CHZ1}^* , t_{CHZ2}^*	-	25	-	30	-	35	ns
Output Disable to Output in High-Z	t_{OHZ}^*	-	25	-	30	-	35	ns
Output Hold from Address Change	t_{OH}	5	-	5	-	5	-	ns

(2) WRITE CYCLE

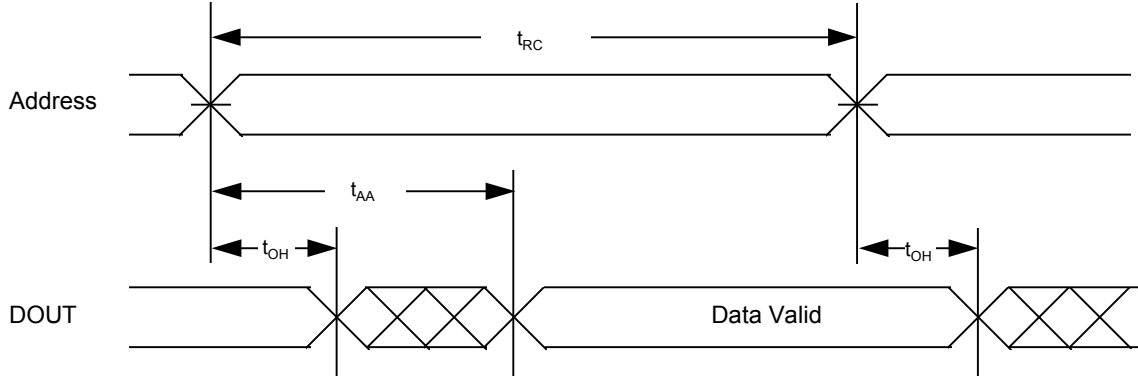
PARAMETER	SYMBOL	UT62W1024-35		UT62W1024-55		UT62W1024-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	35	-	55	-	70	-	ns
Address Valid to End of Write	t_{AW}	30	-	50	-	60	-	ns
Chip Enable to End of Write	t_{CW1} , t_{CW2}	30	-	50	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	25	-	40	-	45	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	20	-	25	-	30	-	ns
Data Hold from End of Write-Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	5	-	5	-	5	-	ns
Write to Output in High-Z	t_{WHZ}^*	-	15	-	20	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.

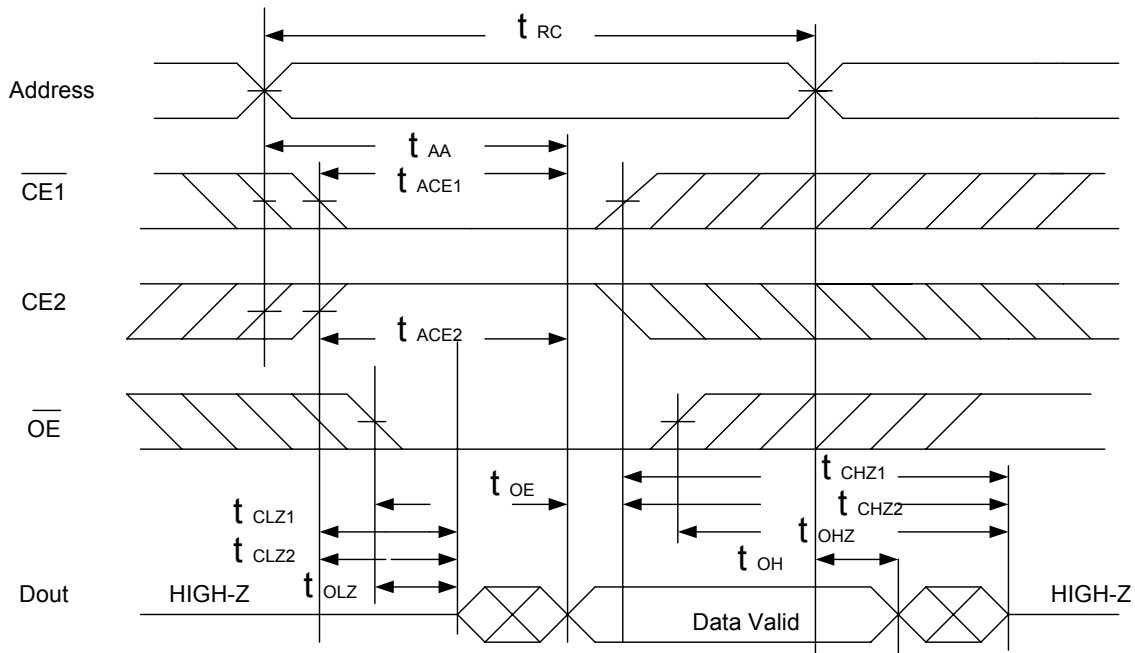


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)



READ CYCLE 2 ($\overline{CE1}$, CE2 and \overline{OE} Controlled) (1,3,5,6)

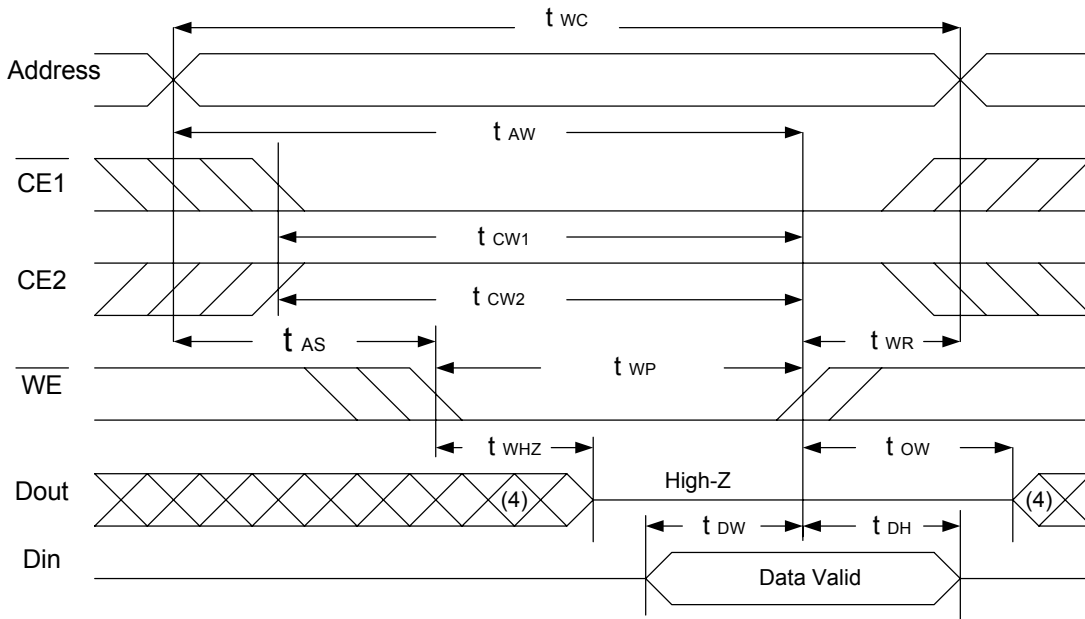


Notes :

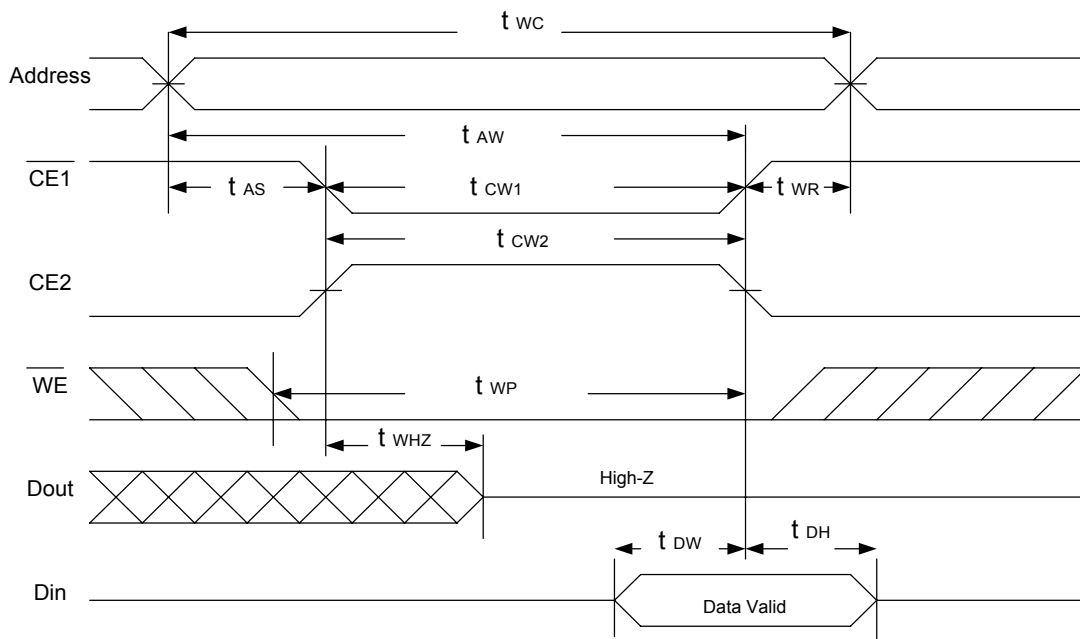
1. \overline{WE} is HIGH for a read cycle.
2. Device is continuously selected \overline{OE} , $\overline{CE1} = V_{IL}$ and $CE2 = V_{IH}$.
3. Address must be valid prior to or coincident with $\overline{CE1}$ low and CE2 high transition; otherwise t_{AA} is the limiting parameter.
4. \overline{OE} is low.
5. t_{CLZ1} , t_{CLZ2} , t_{OLZ} , t_{CHZ1} , t_{CHZ2} and t_{OHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.
6. At any given temperature and voltage condition, t_{CHZ1} is less than t_{CLZ1} , t_{CHZ2} is less than t_{CLZ2} , t_{OHZ} is less than t_{OLZ} .



WRITE CYCLE 1 (\overline{WE} Controlled) (1,2,3,5)



WRITE CYCLE 2 ($\overline{CE1}$ and $\overline{CE2}$ Controlled) (1,2,5)



Notes :

1. \overline{WE} or $\overline{CE1}$ must be HIGH or $\overline{CE2}$ must be LOW during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE1}$, a high $\overline{CE2}$ and a low \overline{WE} .
3. During a \overline{WE} controlled with write cycle with \overline{OE} LOW, t_{wp} must be greater than $t_{whz}+t_{dw}$ to allow the I/O drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
4. If the $\overline{CE1}$ LOW transition occurs simultaneously with or after \overline{WE} LOW transition, the outputs remain in a high Impedance state.
6. t_{ow} and t_{whz} are specified with $C_L=5pF$. Transition is measured $\pm 500mV$ from steady state.



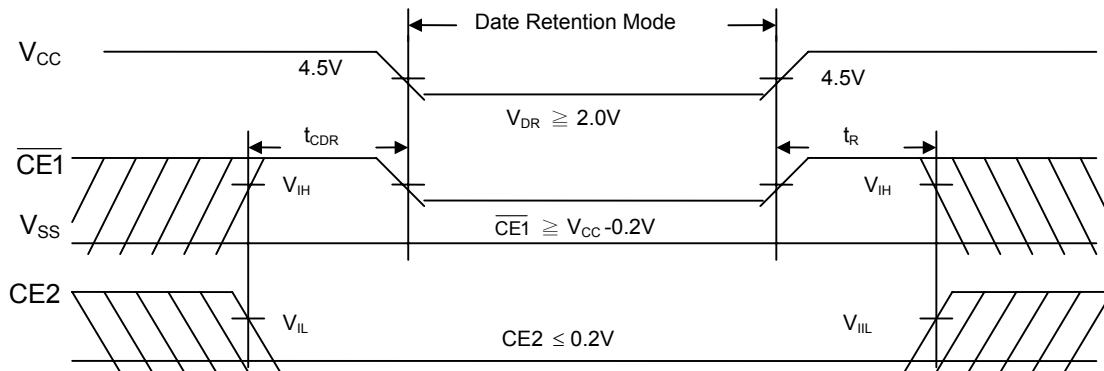
DATA RETENTION CHARACTERISTICS (TA = 0°C to 70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Vcc for Data Retention	V _{DR}	$\overline{CE1} \geq V_{CC}-0.2V$ or $CE2 \leq 0.2V$	2.0	-	-	V	
Data Retention Current	I _{DR}	V _{CC} =3V $\overline{CE1} \geq V_{CC}-0.2V$ or $CE2 \leq 0.2V$	- L	-	2	$\frac{80}{20^*}$	μA
			- LL	-	0.5	$\frac{20}{10^*}$	μA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns	
Recovery Time	t _R		t _{RC} *	-	-	ns	

t_{RC}* = Read Cycle Time

*Those parameters are for reference only under 50°C

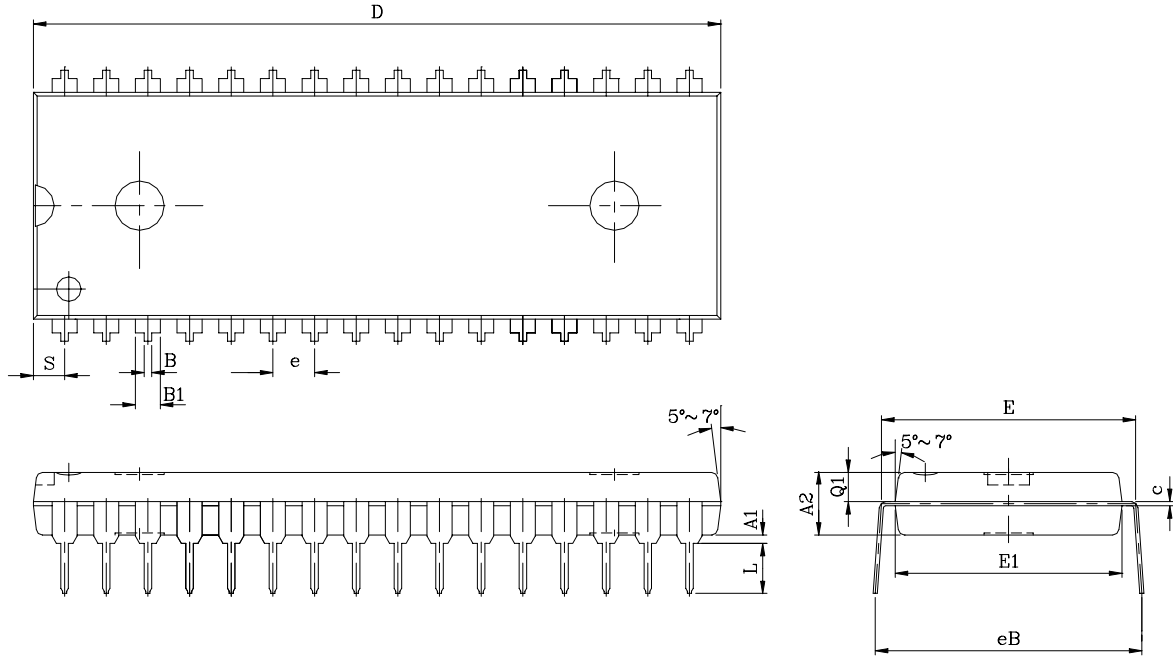
DATA RETENTION WAVEFORM





PACKAGE OUTLINE DIMENSION

32 pin 600 mil PDIP Package Outline Dimension



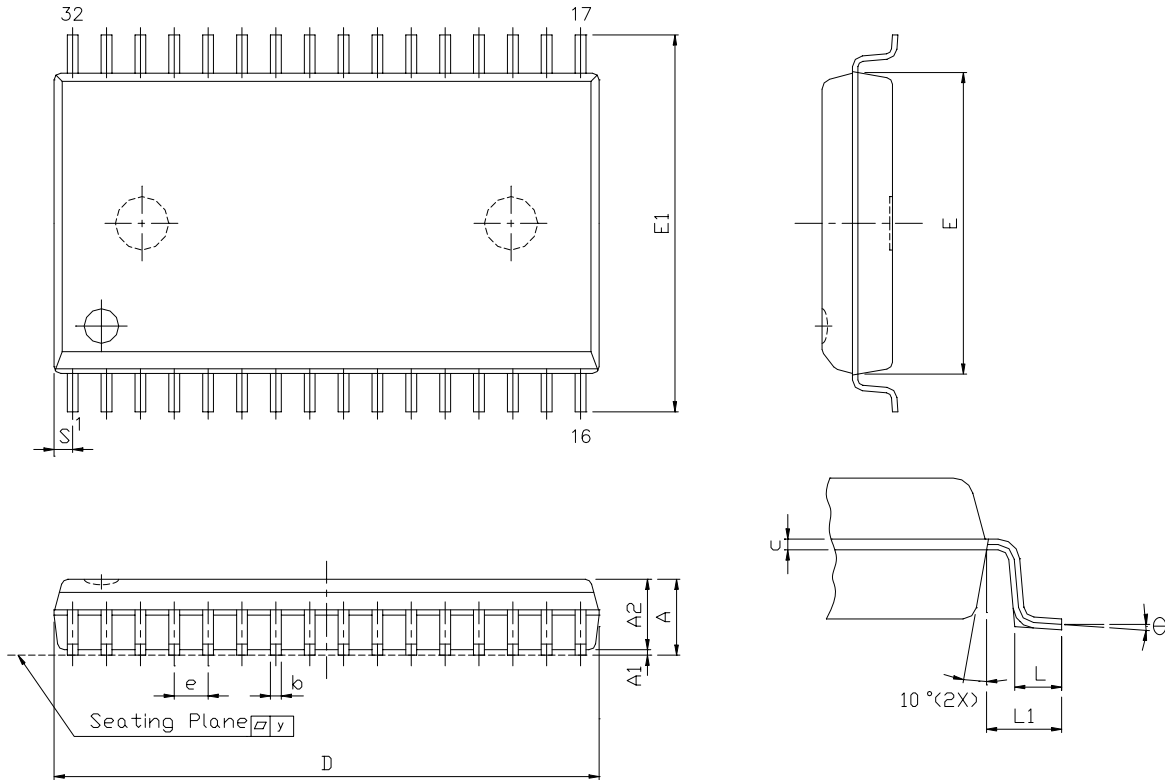
SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A1	0.010 (MIN)	0.254 (MIN)
A2	0.150 ± 0.005	3.810 ± 0.127
B	0.018 ± 0.005	0.457 ± 0.127
B1	0.050 ± 0.005	1.270 ± 0.127
c	0.010 ± 0.004	0.254 ± 0.102
D	1.650 ± 0.005	41.910 ± 0.127
E	0.600 ± 0.010	15.240 ± 0.254
E1	0.544 ± 0.004	13.818 ± 0.102
e	0.100 (TYP)	2.540 (TYP)
eB	0.640 ± 0.020	16.256 ± 0.508
L	0.130 ± 0.010	3.302 ± 0.254
S	0.075 ± 0.010	1.905 ± 0.254
Q1	0.070 ± 0.005	1.778 ± 0.127

Note:

1. D/E1/S DIMENSION DO NOT INCLUDE MOLD FLASH.



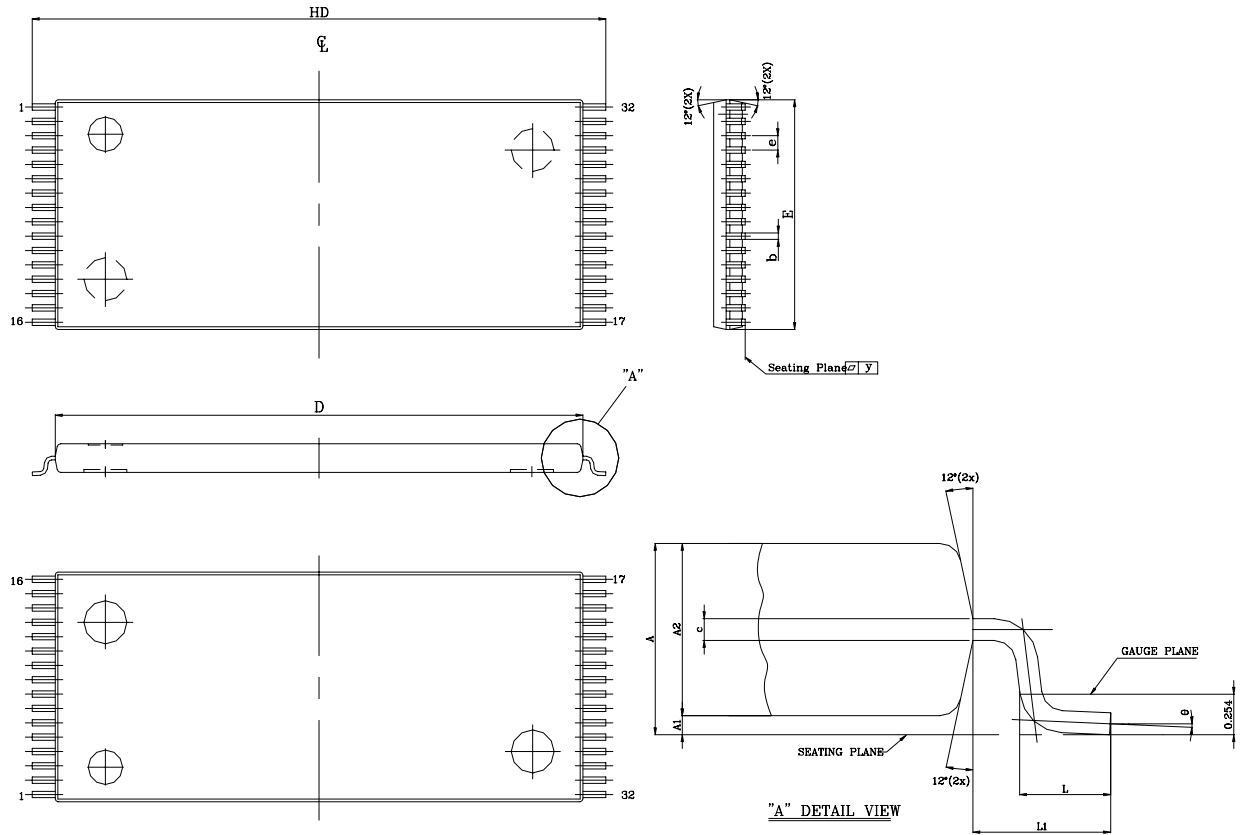
32 pin 450mil SOP Package Outline Dimension



SYMBOL	UNIT	INCH(BASE)	MM(REF)
A		0.118 (MAX)	2.997 (MAX)
A1		0.004(MIN)	0.102(MIN)
A2		0.111(MAX)	2.82(MAX)
b		0.016(TYP)	0.406(TYP)
c		0.008(TYP)	0.203(TYP)
D		0.817(MAX)	20.75(MAX)
E		0.445 ± 0.005	11.303 ± 0.127
E1		0.555 ± 0.012	14.097 ± 0.305
e		0.050(TYP)	1.270(TYP)
L		0.0347 ± 0.008	0.881 ± 0.203
L1		0.055 ± 0.008	1.397 ± 0.203
S		0.026(MAX)	0.066 (MAX)
y		0.004(MAX)	0.101(MAX)
θ		0° -10°	0° -10°



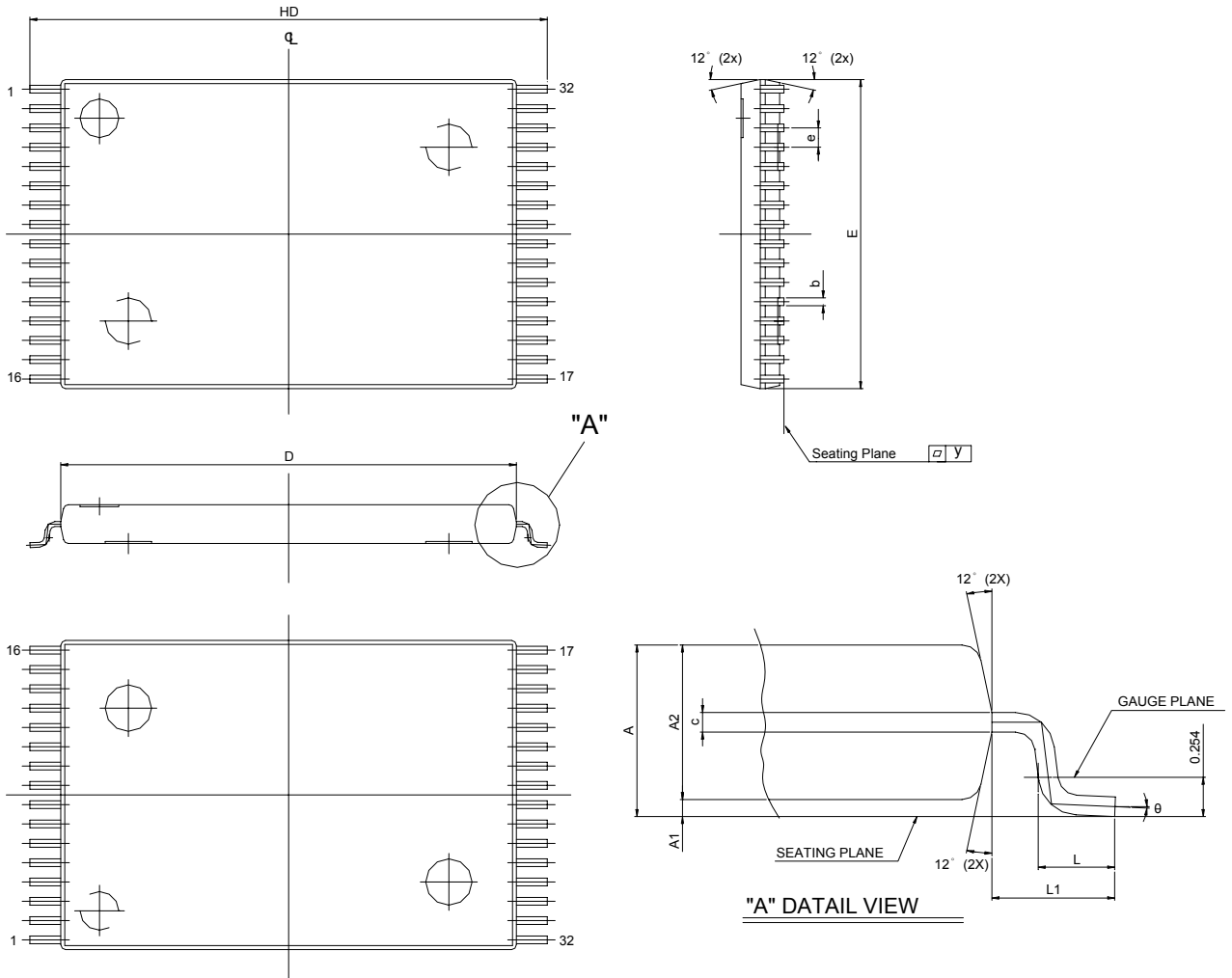
32 pin TSOP-I Package Outline Dimension



SYMBOL	UNIT	INCH(BASE)	MM(REF)
A		0.047 (MAX)	1.20 (MAX)
A1		0.004 ± 0.002	0.10 ± 0.05
A2		0.039 ± 0.002	1.00 ± 0.05
b		0.008 + 0.002 - 0.001	0.20 + 0.05 - 0.03
c		0.005 (TYP)	0.127 (TYP)
D		0.724 ± 0.004	18.40 ± 0.10
E		0.315 ± 0.004	8.00 ± 0.10
e		0.020 (TYP)	0.50 (TYP)
HD		0.787 ± 0.008	20.00 ± 0.20
L		0.0197 ± 0.004	0.50 ± 0.10
L1		0.0315 ± 0.004	0.08 ± 0.10
y		0.003 (MAX)	0.076 (MAX)
⊖		0° ~ 5°	0° ~ 5°



32 pin 8mm x 13.4mm STSOP Package Outline Dimension



UNIT	INCH(BASE)	MM(REF)
A	0.049 (MAX)	1.25 (MAX)
A1	0.005 ± 0.002	0.130 ± 0.05
A2	0.039 ± 0.002	1.00 ± 0.05
b	0.008 ± 0.01	0.20 ± 0.025
c	0.005 (TYP)	0.127 (TYP)
D	0.465 ± 0.004	11.80 ± 0.10
E	0.315 ± 0.004	8.00 ± 0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.528 ± 0.008	13.40 ± 0.20
L	0.0197 ± 0.004	0.50 ± 0.10
L1	0.0315 ± 0.004	0.8 ± 0.10
y	0.003 (MAX)	0.076 (MAX)
θ	0° ~ 5°	0° ~ 5°





ORDERING INFORMATION

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A)	PACKAGE
UT62W1024PC-35L	35	500	32 PIN PDIP
UT62W1024PC-35LL	35	50	32 PIN PDIP
UT62W1024SC-35L	35	500	32 PIN SOP
UT62W1024SC-35LL	35	50	32 PIN SOP
UT62W1024LC-35L	35	500	32 PIN TSOP-I
UT62W1024LC-35LL	35	50	32 PIN TSOP-I
UT62W1024LS-35L	35	500	32 PIN STSOP
UT62W1024LS-35LL	35	50	32 PIN STSOP
UT62W1024PC-55L	55	500	32 PIN PDIP
UT62W1024PC-55LL	55	50	32 PIN PDIP
UT62W1024SC-55L	55	500	32 PIN SOP
UT62W1024SC-55LL	55	50	32 PIN SOP
UT62W1024LC-55L	55	500	32 PIN TSOP-I
UT62W1024LC-55LL	55	50	32 PIN TSOP-I
UT62W1024LS-55L	55	500	32 PIN STSOP
UT62W1024LS-55LL	55	50	32 PIN STSOP
UT62W1024PC-70L	70	500	32 PIN PDIP
UT62W1024PC-70LL	70	50	32 PIN PDIP
UT62W1024SC-70L	70	500	32 PIN SOP
UT62W1024SC-70LL	70	50	32 PIN SOP
UT62W1024LC-70L	70	500	32 PIN TSOP-I
UT62W1024LC-70LL	70	50	32 PIN TSOP-I
UT62W1024LS-70L	70	500	32 PIN STSOP
UT62W1024LS-70LL	70	50	32 PIN STSOP



UTRON

UT62W1024

Rev. 1.0

128K X 8 BIT WIDE RANGE LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	DATE
REV. 0.9	Original.	Mar.15. 2001
REV. 1.0	1. The symbols CE1# ,OE# & WE# are revised as $\overline{CE1}$, \overline{OE} & \overline{WE} . 2. I_{cc1} is revise as I_{cc} . 3. I_{cc2} is revise as I_{cc1} .	Jul. 06. 2001



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Rev. 1.0

UT62W1024
128K X 8 BIT WIDE RANGE LOW POWER CMOS SRAM

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